120 dB

1.3 μV/°C

0.11 V/µs

0.01% at 1 kHz

3 mV

2 fA

National Semiconductor

March 1998

## **LPC662**

# **Low Power CMOS Dual Operational Amplifier**

### **General Description**

The LPC662 CMOS Dual operational amplifier is ideal for operation from a single supply. It features a wide range of operating voltage from +5V to +15V, rail-to-rail output swing in addition to an input common-mode range that includes ground. Performance limitations that have plagued CMOS amplifiers in the past are not a problem with this design. Input  $V_{\text{OS}},$  drift, and broadband noise as well as voltage gain (into  $100~\text{k}\Omega$  and  $5~\text{k}\Omega)$  are all equal to or better than widely accepted bipolar equivalents, while the power supply requirement is typically less than 0.5~mW.

This chip is built with National's advanced Double-Poly Silicon-Gate CMOS process.

See the LPC660 datasheet for a Quad CMOS operational amplifier and LPC661 for a single CMOS operational amplifier with these same features.

### **Applications**

- High-impedance buffer
- Precision current-to-voltage converter

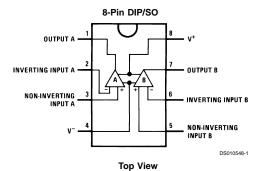
- Long-term integrator
- High-impedance preamplifier
- Active filter
- Sample-and-Hold circuit
- Peak detector

### **Features**

- Rail-to-rail output swing
- Micropower operation (<0.5 mW)
- Specified for 100 kΩ and 5 kΩ loads
- High voltage gain
- Low input offset voltage
- Low offset voltage drift
- Ultra low input bias current
- Input common-mode includes GND
- Operating range from +5V to +15V
- Low distortion
- Slew rate

### ■ Full military temperature range available

## **Connection Diagram**



## **Ordering Information**

Package	Temperatu	re Range	NSC	Transport	
	Military	Industrial	Drawing	Media	
8-Pin	LPC662AMD		D08C	Rail	
Side Brazed					
Ceramic DIP					
8-Pin		LPC662AIM	M08A	Rail	
Small Outline		or LPC662IM		Tape and Reel	
8-Pin		LPC662AIN	N08E	Rail	
Molded DIP		or LPC662IN			
8-Pin	LPC662AMJ/883		J08A	Rail	
Ceramic DIP					

## Absolute Maximum Ratings (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Differential Input Voltage ±Supply Voltage Supply Voltage  $(V^+ - V^-)$ 16V Output Short Circuit to V+ (Note 11)

Output Short Circuit to V-Lead Temperature

(Soldering, 10 sec.) 260°C Storage Temp. Range -65°C to +150°C

Junction Temperature

**ESD** Rating

 $(C = 100 pF, R = 1.5 k\Omega)$ Power Dissipation Current at Input Pin Current at Output Pin ±18 mA

150°C

1000V (Note 2) ±5 mA

(Note 1)

Current at Power Supply Pin 35 mA Voltage at Input/Output Pin  $(V^{+}) + 0.3V$ ,  $(V^{-}) -0.3V$ 

# **Operating Ratings** (Note 3)

Temperature Range

LPC662AMJ/883  $-55^{\circ}C \le T_{J} \le +125^{\circ}C$ LPC662AM  $-55^{\circ}C \leq T_{J} \leq +125^{\circ}C$ LPC662AI  $-40^{\circ}C \leq T_{J} \leq +85^{\circ}C$ LPC662I  $-40^{\circ}C \leq T_{J} \leq +85^{\circ}C$ Supply Range 4.75V to 15.5V Power Dissipation (Note 9)

Thermal Resistance  $(\theta_{JA})$  (Note 10)

8-Pin Ceramic DIP 100°C/W 8-Pin Molded DIP 101°C/W 165°C/W 8-Pin SO 8-Pin Side Brazed Ceramic DIP 100°C/W

### **DC Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}C$ . **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)			
Input Offset Voltage		1	3	3	6	mV
			3.5	3.3	6.3	max
Input Offset Voltage		1.3				μV/°C
Average Drift						
Input Bias Current		0.002	20			pА
			100	4	4	max
Input Offset Current		0.001	20			pА
			100	2	2	max
Input Resistance		>1				Tera Ω
Common Mode	$0V \le V_{CM} \le 12.0V$	83	70	70	63	dB
Rejection Ratio	V+ = 15V		68	68	61	min
Positive Power Supply	5V ≤ V <sup>+</sup> ≤ 15V	83	70	70	63	dB
Rejection Ratio	V <sub>O</sub> = 2.5V		68	68	61	min
Negative Power Supply	$0V \le V^- \le -10V$	94	84	84	74	dB
Rejection Ratio			82	83	73	min
Input Common-Mode	V+ = 5V and 15V	-0.4	-0.1	-0.1	-0.1	V
Voltage Range	For CMRR ≥ 50 dB		0	0	0	max
		V <sup>+</sup> – 1.9	V <sup>+</sup> - 2.3	V <sup>+</sup> - 2.3	V <sup>+</sup> – 2.3	V
			V+ - 2.6	V+ - 2.5	V+ - 2.5	min
Large Signal	$R_L = 100 \text{ k}\Omega \text{ (Note 5)}$	1000	400	400	300	V/mV
Voltage Gain	Sourcing		250	300	200	min
	Sinking	500	180	180	90	V/mV
			70	120	70	min
	$R_L = 5 \text{ k}\Omega \text{ (Note 5)}$	1000	200	200	100	V/mV
	Sourcing		150	160	80	min
	Sinking	250	100	100	50	V/mV
			35	60	40	min

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# DC Electrical Characteristics (Continued)

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Unless otherwise specified, all limits guaranteed for  $T_J$  = 25°C. **Boldface** limits apply at the temperature extremes.  $V^+$  = 5V,  $V^-$  = 0V,  $V_{CM}$  = 1.5V,  $V_O$  = 2.5V and  $R_L$  > 1M unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)	, ,	,	
Output Swing	V+ = 5V	4.987	4.970	4.970	4.940	V
	$R_{L} = 100 \text{ k}\Omega \text{ to V}^{+}/2$		4.950	4.950	4.910	min
		0.004	0.030	0.030	0.060	V
			0.050	0.050	0.090	max
	V+ = 5V	4.940	4.850	4.850	4.750	V
	$R_L = 5 k\Omega \text{ to V}^+/2$		4.750	4.750	4.650	min
		0.040	0.150	0.150	0.250	V
			0.250	0.250	0.350	max
	V+ = 15V	14.970	14.920	14.920	14.880	V
	$R_{L} = 100 \text{ k}\Omega \text{ to V}^{+}/2$		14.880	14.880	14.820	min
		0.007	0.030	0.030	0.060	V
			0.050	0.050	0.090	max
	V+ = 15V	14.840	14.680	14.680	14.580	V
	$R_L = 5 k\Omega \text{ to V}^+/2$		14.600	14.600	14.480	min
		0.110	0.220	0.220	0.320	V
			0.300	0.300	0.400	max
Output Current	Sourcing, V <sub>O</sub> = 0V	22	16	16	13	mA
V <sup>+</sup> = 5V			12	14	11	min
	Sinking, V <sub>O</sub> = 5V	21	16	16	13	mA
			12	14	11	min
Output Current	Sourcing, V <sub>O</sub> = 0V	40	19	28	23	mA
V <sup>+</sup> = 15V			19	25	20	min
	Sinking, V <sub>O</sub> = 13V	39	19	28	23	mA
	(Note 11)		19	24	19	min
Supply Current	Both Amplifiers	86	120	120	140	μΑ
	V <sub>O</sub> = 1.5V		145	140	160	max

### **AC Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $T_J$  = 25°C. **Boldface** limits apply at the temperature extremes.  $V^+$  = 5V,  $V^-$  = 0V,  $V_{CM}$  = 1.5V,  $V_O$  = 2.5V and  $R_L$  > 1M unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)			
Slew Rate	(Note 6)	0.11	0.07	0.07	0.05	V/µs
			0.04	0.05	0.03	min
Gain-Bandwidth Product		0.35				MHz
Phase Margin		50				Deg
Gain Margin		17				dB
Amp-to-Amp Isolation	(Note 7)	130				dB
Input Referred Voltage Noise	F = 1 kHz	42				nV/√Hz
Input Referred Current Noise	F = 1 kHz	0.0002				pA/√Hz
Total Harmonic Distortion	$F = 1 \text{ kHz}, A_V = -10, V^+ = 15V$	0.01				%
	$R_L = 100 \text{ k}\Omega, V_O = 8 V_{PP}$					

Note 1: Applies to both single supply and split supply operation. Continuous short circuit operation at elevated ambient temperature and/or multiple Op Amp shorts can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.

Note 2: The maximum power dissipation is a function of  $T_{J(max)}$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation of any ambient temperature is  $P_D = (T_{J(max)} - T_A)\theta_{JA}$ .

Note 3: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

Note 4: Limits are guaranteed by testing or correlation.

Note 5:  $V^+$  = 15V,  $V_{CM}$  = 7.5V and  $R_L$  connected to 7.5V. For Sourcing tests, 7.5V  $\leq$   $V_O$   $\leq$  11.5V. For Sinking tests, 2.5V  $\leq$   $V_O$   $\leq$  7.5V.

Note 6: V+ = 15V. Connected as Voltage Follower with 10V step input. Number specified is the slower of the positive and negative slew rates.

Note 7: Input referred.  $V^+$  = 15V and  $R_L$  = 100 k $\Omega$  connected to  $V^+$ /2. Each amp excited in turn with 1 kHz to produce  $V_O$  = 13  $V_{PP}$ .

Note 8: A military RETS electrical test specification is available on request. At the time of printing, the LPC662AMJ/883 RETS specification complied fully with the

boldface limits in this column. The LPC662AMJ/883 may also be procured to a Standard Military Drawing specification.

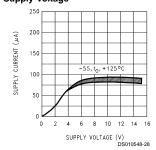
Note 9: For operating at elevated temperatures the device must be derated based on the thermal resistance  $\theta_{JA}$  with  $P_D = (T_J - T_A)/\theta_{JA}$ .

Note 10: All numbers apply for packages soldered directly into a PC board.

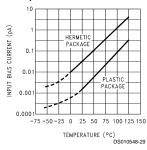
Note 11: Do not connect output to V<sup>+</sup>when V<sup>+</sup> is greater than 13V or reliability may be adversely affected.

# Typical Performance Characteristics $V_S = \pm 7.5 V$ , $T_A = 25 ^{\circ} C$ unless otherwise specified

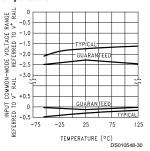
### Supply Current vs Supply Voltage



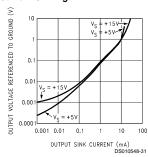
# Input Bias Current vs Temperature



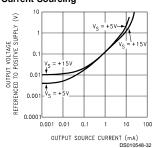
#### Input Common-Mode Voltage Range vs Temperature



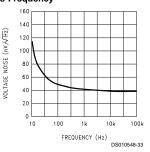
#### Output Characteristics Current Sinking



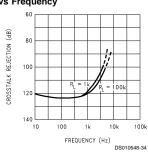
#### Output Characteristics Current Sourcing



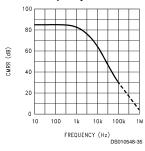
# Input Voltage Noise vs Frequency



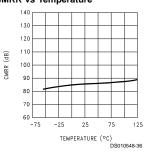
# Crosstalk Rejection vs Frequency



# CMRR vs Frequency



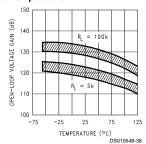
### CMRR vs Temperature



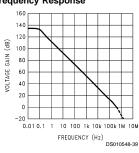
5

# Typical Performance Characteristics $V_S$ = $\pm 7.5V$ , $T_A$ = $25^{\circ}C$ unless otherwise specified (Continued)

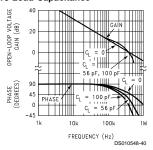
# Open-Loop Voltage Gain vs Temperature



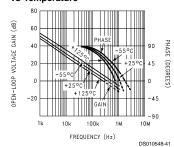
### Open-Loop Frequency Response



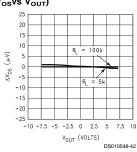
# Gain and Phase Responses vs Load Capacitance



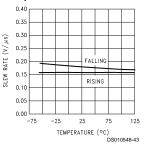
# Gain and Phase Responses vs Temperature



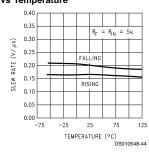
### Gain Error (V<sub>OS</sub>vs V<sub>OUT</sub>)



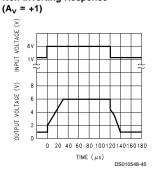
# Non-Inverting Slew Rate vs Temperature



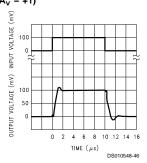
# Inverting Slew Rate vs Temperature



### Large-Signal Pulse Non-Inverting Response

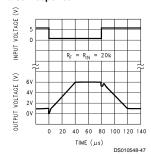


#### Non-Inverting Small Signal Pulse Response (A<sub>V</sub> = +1)

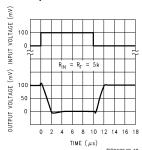


## Typical Performance Characteristics $V_S = \pm 7.5V$ , $T_A = 25^{\circ}C$ unless otherwise specified (Continued)

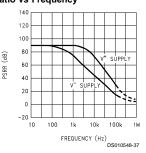
# Inverting Large-Signal Pulse Response



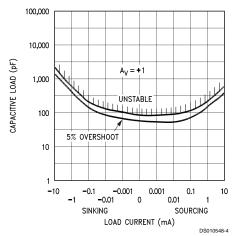
#### Inverting Small-Signal Pulse Response



#### Power Supply Rejection Ratio vs Frequency

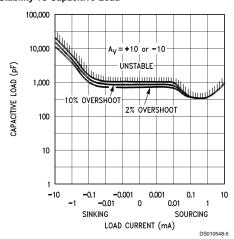


#### Stability vs Capacitive Load



# Note: Avoid resistive loads of less than $500\Omega$ , as they may cause instability.

### Stability vs Capacitive Load



## **Application Hints**

#### AMPLIFIER TOPOLOGY

The topology chosen for the LPC662 is unconventional (compared to general-purpose op amps) in that the traditional unity-gain buffer output stage is not used; instead, the output is taken directly from the output of the integrator, to allow rail-to-rail output swing. Since the buffer traditionally delivers the power to the load, while maintaining high op amp gain and stability, and must withstand shorts to either rail, these tasks now fall to the integrator.

As a result of these demands, the integrator is a compound affair with an embedded gain stage that is doubly fed forward (via  $C_{\rm f}$  and  $C_{\rm ff}$ ) by a dedicated unity-gain compensation driver. In addition, the output portion of the integrator is a push-pull configuration for delivering heavy loads. While sinking current the whole amplifier path consists of three gain stages with one stage fed forward, whereas while sourcing the path contains four gain stages with two fed

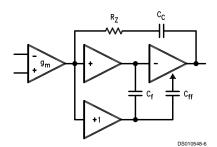


FIGURE 1. LPC662 Circuit Topology (Each Amplifier)

The large signal voltage gain while sourcing is comparable to traditional bipolar op amps for load resistance of at least 5 k $\Omega$ . The gain while sinking is higher than most CMOS op

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### **Application Hints** (Continued)

amps, due to the additional gain stage; however, when driving load resistance of 5 k $\Omega$  or less, the gain will be reduced as indicated in the Electrical Characteristics. The op amp can drive load resistance as low as  $500\Omega$  without instability.

### COMPENSATING INPUT CAPACITANCE

Refer to the LMC660 or LMC662 datasheets to determine whether or not a feedback capacitor will be necessary for compensation and what the value of that capacitor would be.

#### CAPACITIVE LOAD TOLERANCE

Like many other op amps, the LPC662 may oscillate when its applied load appears capacitive. The threshold of oscillation varies both with load and circuit gain. The configuration most sensitive to oscillation is a unity-gain follower. See the Typical Performance Characteristics.

The load capacitance interacts with the op amp's output resistance to create an additional pole. If this pole frequency is sufficiently low, it will degrade the op amp's phase margin so that the amplifier is no longer stable at low gains. The addition of a small resistor (50 $\Omega$  to  $100\Omega$ ) in series with the op amp's output, and a capacitor (5 pF to 10 pF) from inverting input to output pins, returns the phase margin to a safe value without interfering with lower-frequency circuit operation. Thus, larger values of capacitance can be tolerated without oscillation. Note that in all cases, the output will ring heavily when the load capacitance is near the threshold for oscillation.

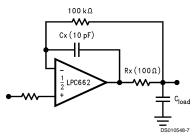


FIGURE 2. Rx, Cx Improve Capacitive Load Tolerance

Capacitive load driving capability is enhanced by using a pull up resistor to V<sup>+</sup> Figure 3. Typically a pull up resistor conducting 50 µA or more will significantly improve capacitive load responses. The value of the pull up resistor must be determined based on the current sinking capability of the

amplifier with respect to the desired output swing. Open loop gain of the amplifier can also be affected by the pull up resistor (see Electrical Characteristics).

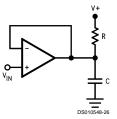


FIGURE 3. Compensating for Large Capacitive Loads with A Pull Up Resistor

# PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LPC662, typically less than 0.04 pA, it is essential to have an excellent layout. Fortunately, the techniques for obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LPC662's inputs and the terminals of capacitors, diodes, conductors, resistors, relay terminals, etc. connected to the op-amp's inputs. See Figure  $\emph{4}.$  To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of 1012 ohms, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of an input. This would cause a 100 times degradation from the LPC662's actual performance. However, if a guard ring is held within 5 mV of the inputs, then even a resistance of 1011 ohms would cause only 0.05 pA of leakage current, or perhaps a minor (2:1) degradation of the amplifier's performance. See Figure 5a, Figure 5b, Figure 5c for typical connections of guard rings for standard op-amp configurations. If both inputs are active and at high impedance, the guard can be tied to ground and still provide some protection; see Figure 5d.

## Application Hints (Continued)

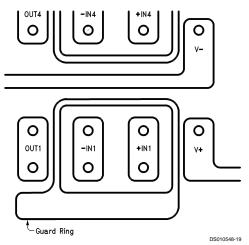
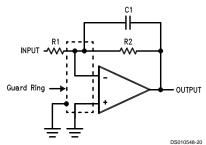
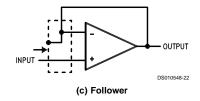
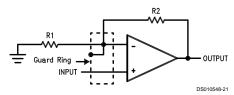


FIGURE 4. Example of Guard Ring in P.C. Board Layout, using the LPC660

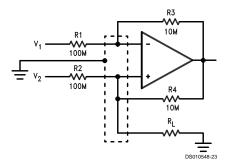




## (a) Inverting Amplifier



(b) Non-Inverting Amplifier



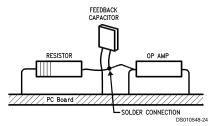
(d) Howland Current Pump

## FIGURE 5. Guard Ring Connections

The designer should be aware that when it is inappropriate to lay out a PC board for the sake of just a few circuits, there is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may have to forego some of the advantages of PC board con-

struction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See  $Figure\ 6$ .

## **Application Hints** (Continued)



(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board.)

### FIGURE 6. Air Wiring

#### **BIAS CURRENT TESTING**

The test method of *Figure 7* is appropriate for bench-testing bias current with reasonable accuracy. To understand its operation, first close switch S2 momentarily. When S2 is opened, then

$$I^{-} = \frac{dV_{OUT}}{dt} \times C2.$$

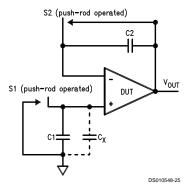


FIGURE 7. Simple Input Bias Current Test Circuit

A suitable capacitor for C2 would be a 5 pF or 10 pF silver mica, NPO ceramic, or air-dielectric. When determining the magnitude of  $I^-$ , the leakage of the capacitor and socket must be taken into account. Switch S2 should be left shorted most of the time, or else the dielectric absorption of the capacitor C2 could cause errors.

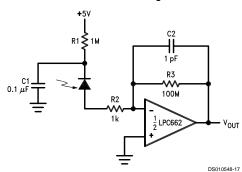
Similarly, if S1 is shorted momentarily (while leaving S2 shorted)  $\,$ 

$$I^{+} = \frac{dV_{OUT}}{dt} \times (C1 + C_{x})$$

where  $C_{\mathsf{x}}$  is the stray capacitance at the + input.

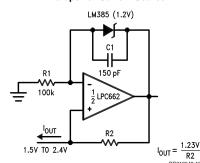
# Typical Single-Supply Applications ( $V^+ = 5.0 V_{DC}$ )

### Photodiode Current-to-Voltage Converter



Note: A 5V bias on the photodiode can cut its capacitance by a factor of 2 or 3, leading to improved response and lower noise. However, this bias on the photodiode will cause photodiode leakage (also known as its dark current).

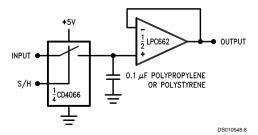
## Micropower Current Source



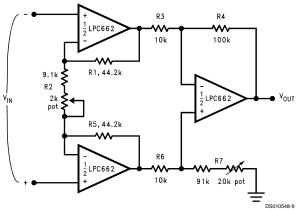
**Note:** (Upper limit of output range dictated by input common-mode range; lower limit dictated by minimum current requirement of LM385.)

# Typical Single-Supply Applications (V<sup>+</sup> = $5.0 V_{DC}$ ) (Continued)

### Low-Leakage Sample-and-Hold



### Instrumentation Amplifier



If R1 = R5, R3 = R6 and R4 = R7; then

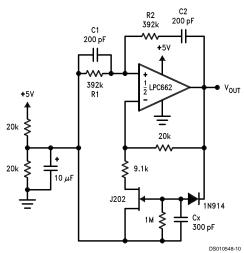
$$\frac{V_{OUT}}{V_{IN}} = \frac{R2 + 2R1}{R2} \times \frac{R4}{R3}$$

 $\frac{SSV}{V_{IN}} = \frac{SSV}{R2} \times \frac{SSV}{R3}$  $\therefore A_V \approx 100$  for circuit shown.

For good CMRR over temperature, low drift resistors should be used. Matching of R3 to R6 and R4 to R7 affects CMRR. Gain may be adjusted through R2. CMRR may be adjusted through R7.

# Typical Single-Supply Applications $(V^+ = 5.0 V_{DC})$ (Continued)

## Sine-Wave Oscillator



Oscillator frequency is determined by R1, R2, C1, and C2:

 $f_{OSC} = 1/2\pi RC$ 

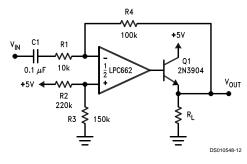
where R = R1 = R2 and C = C1 = C2.

This circuit, as shown, oscillates at 2.0 kHz with a peak-to-peak output swing of 4.5V

### 1 Hz Square-Wave Oscillator

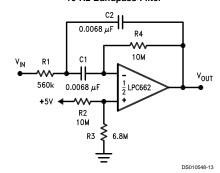
# 

### Power Amplifier



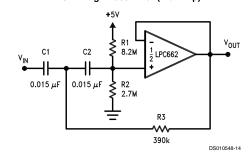
# Typical Single-Supply Applications (V<sup>+</sup> = $5.0 V_{DC}$ ) (Continued)

## 10 Hz Bandpass Filter



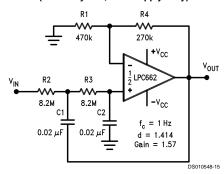
f<sub>O</sub> = 10 Hz Q = 2.1 Gain = -8.8

## 10 Hz High-Pass Filter (2 dB Dip)

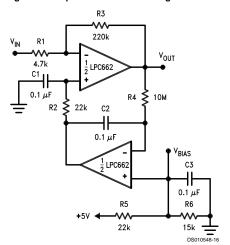


f<sub>c</sub> = 10 Hz d = 0.895 Gain = 1

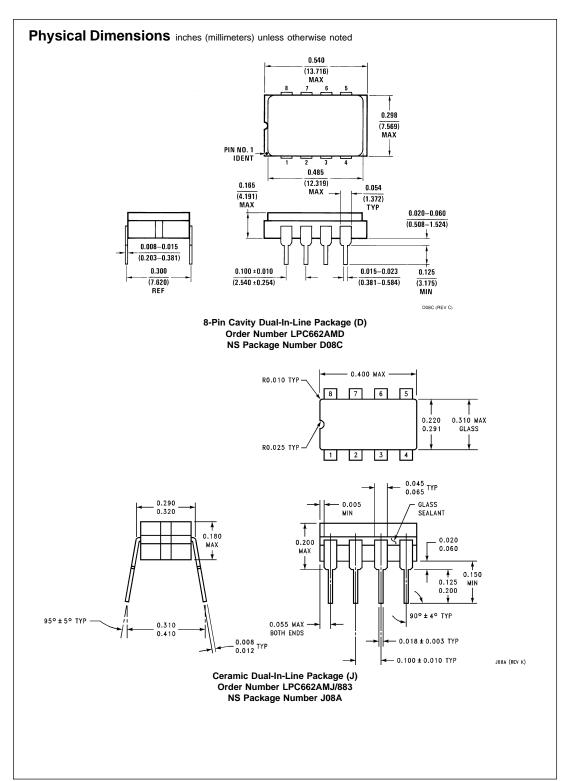
#### 1 Hz Low-Pass Filter (Maximally Flat, Dual Supply Only)



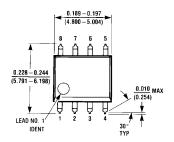
### High Gain Amplifier with Offset Voltage Reduction

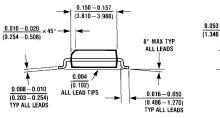


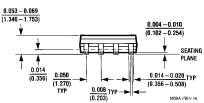
 $\label{eq:Gain} \begin{tabular}{ll} Gain = -46.8 \\ Output offset voltage reduced to the level of the input offset voltage of the bottom amplifier (typically 1 mV), referred to $V_{BIAS}$. \end{tabular}$ 



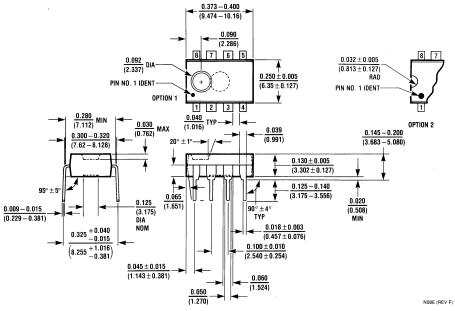
## Physical Dimensions inches (millimeters) unless otherwise noted (Continued)







8-Pin Small Outline Molded Package (M) Order Number LPC662AIM or LPC662IM NS Package Number M08A



8-Pin Molded Dual-In-Line Package (N) Order Number LPC662AIN or LPC662IN NS Package Number N08E

### **Notes**

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